

**ABSTRACT OF THE INVENTION**

The invention relates to a novel CMP slurry composition used for polishing metals, the composition comprising: (a) a dispersion solution comprising an abrasive; and  
5 (b) an oxidizer. The slurry composition has a large particle count of less than about 150,000 particles having a particle size greater than 0.5  $\mu\text{m}$  in 30  $\mu\text{L}$  of slurry, which is achieved by filtering the slurry composition prior to use. Also, the inclusion of a chemical activity enhancer, such as, an amine and a corrosion inhibitor, results in the appropriate copper removal rate without increasing static etch rates.

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